



# PSMN2R0-60ES

N-channel 60 V 2.2 m $\Omega$  standard level MOSFET in I2PAK

Rev. 02 — 19 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

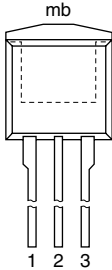
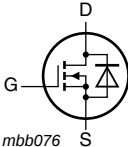
| Symbol                  | Parameter                                    | Conditions                                                                                                                               | Min                 | Typ | Max | Unit |    |
|-------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------|---------------------|-----|-----|------|----|
| V <sub>DS</sub>         | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C                                                                                          | -                   | -   | 60  | V    |    |
| I <sub>D</sub>          | drain current                                | T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <a href="#">Figure 1</a>                                                            | <a href="#">[1]</a> | -   | 120 | A    |    |
| P <sub>tot</sub>        | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>                                                                                    | -                   | -   | 338 | W    |    |
| T <sub>j</sub>          | junction temperature                         |                                                                                                                                          | -55                 | -   | 175 | °C   |    |
| Static characteristics  |                                              |                                                                                                                                          |                     |     |     |      |    |
| R <sub>DSon</sub>       | drain-source on-state resistance             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <a href="#">Figure 12</a>                                     | <a href="#">[2]</a> | -   | 1.8 | 2.2  | mΩ |
|                         |                                              | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>    | -                   | 3   | 3.5 | mΩ   |    |
| Dynamic characteristics |                                              |                                                                                                                                          |                     |     |     |      |    |
| Q <sub>GD</sub>         | gate-drain charge                            | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 75 A;                                                                                           | -                   | 32  | -   | nC   |    |
| Q <sub>G(tot)</sub>     | total gate charge                            | V <sub>DS</sub> = 30 V; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>                                                    | -                   | 137 | -   | nC   |    |
| Avalanche ruggedness    |                                              |                                                                                                                                          |                     |     |     |      |    |
| E <sub>DS(AL)S</sub>    | non-repetitive drain-source avalanche energy | V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 60 V; R <sub>GS</sub> = 50 Ω; Unclamped | -                   | -   | 913 | mJ   |    |

nexperia

[1] Continuous current limited by package.  
[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | G      | gate                              |  |  |
| 2   | D      | drain                             |                                                                                   |                                                                                     |
| 3   | S      | source                            |                                                                                   |                                                                                     |
| mb  | D      | mounting base; connected to drain |                                                                                   |                                                                                     |

SOT226 (I2PAK)

3. Ordering information

Table 3. Ordering information

| Type number  | Package |                                              |         |
|--------------|---------|----------------------------------------------|---------|
|              | Name    | Description                                  | Version |
| PSMN2R0-60ES | I2PAK   | plastic single-ended package (I2PAK); TO-262 | SOT226  |

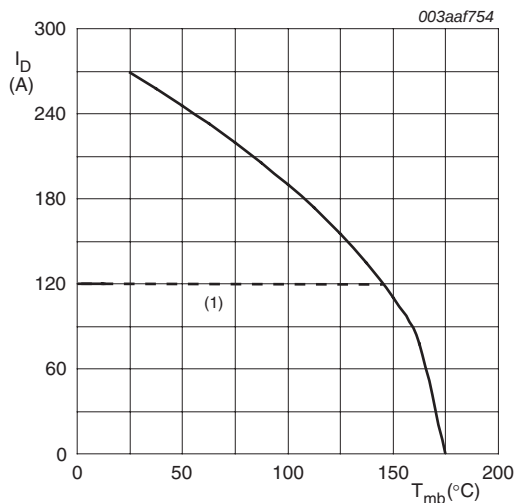
## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

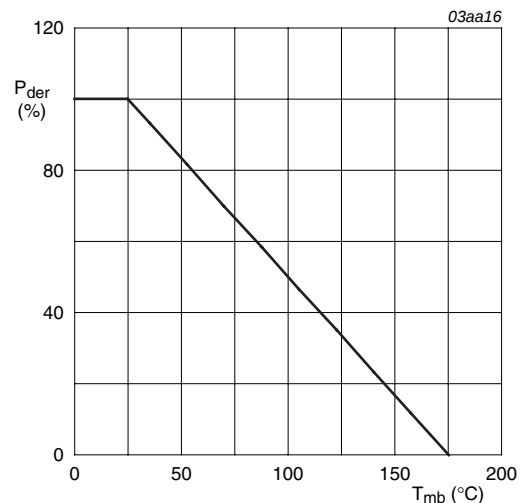
| Symbol                      | Parameter                                    | Conditions                                                                                                                                                    | Min | Max  | Unit |
|-----------------------------|----------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|
| $V_{DS}$                    | drain-source voltage                         | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                                                                                            | -   | 60   | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                                                                             | -   | 60   | V    |
| $V_{GS}$                    | gate-source voltage                          |                                                                                                                                                               | -20 | 20   | V    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>                                                                              | [1] | 120  | A    |
|                             |                                              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>                                                                               | [1] | 120  | A    |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>                                                             | -   | 1135 | A    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>                                                                                                        | -   | 338  | W    |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                               | -55 | 175  | °C   |
| $T_j$                       | junction temperature                         |                                                                                                                                                               | -55 | 175  | °C   |
| $T_{sld(M)}$                | peak soldering temperature                   |                                                                                                                                                               | -   | 260  | °C   |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                               |     |      |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                                       | [1] | 120  | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                            | -   | 1135 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                               |     |      |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 120\text{ A}$ ;<br>$V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; Unclamped | -   | 913  | mJ   |

[1] Continuous current limited by package



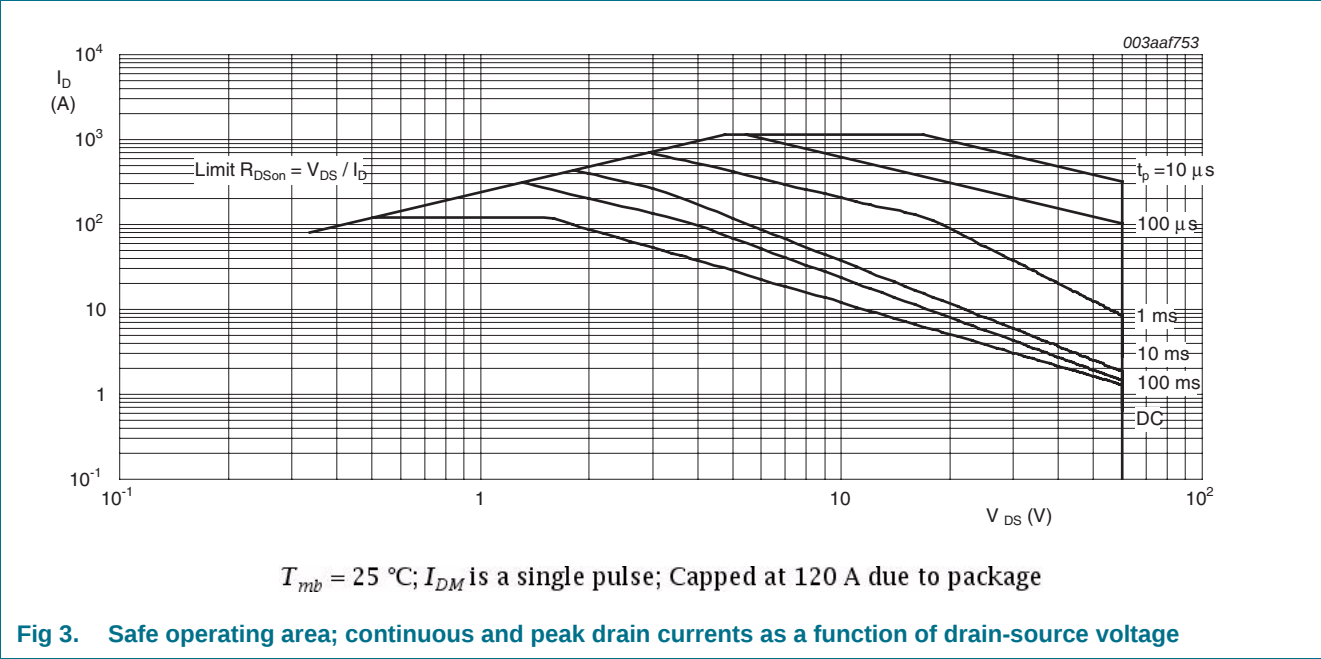
$V_{GS} \geq 10\text{ V}$ (1) Capped at 120 A due to package

**Fig 1. Continuous drain current as a function of mounting base temperature.**



$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

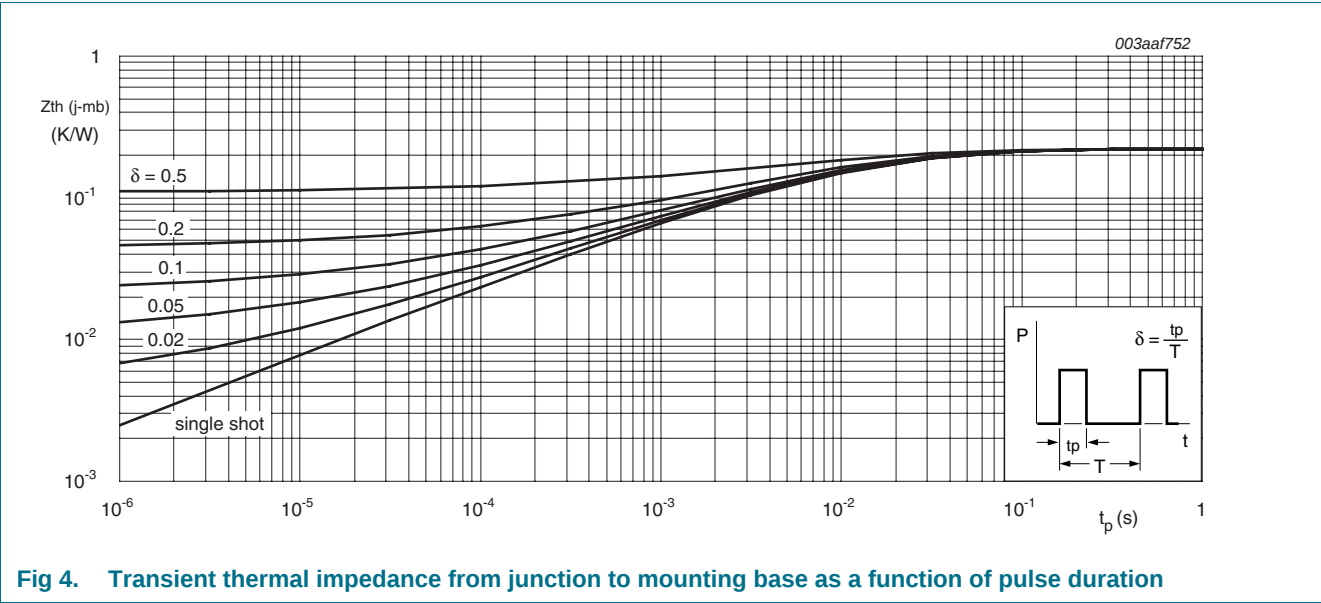
**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                   | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <a href="#">Figure 4</a> | -   | 0.22 | 0.44 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Vertical in free air         | -   | 60   | -    | K/W  |



## 6. Characteristics

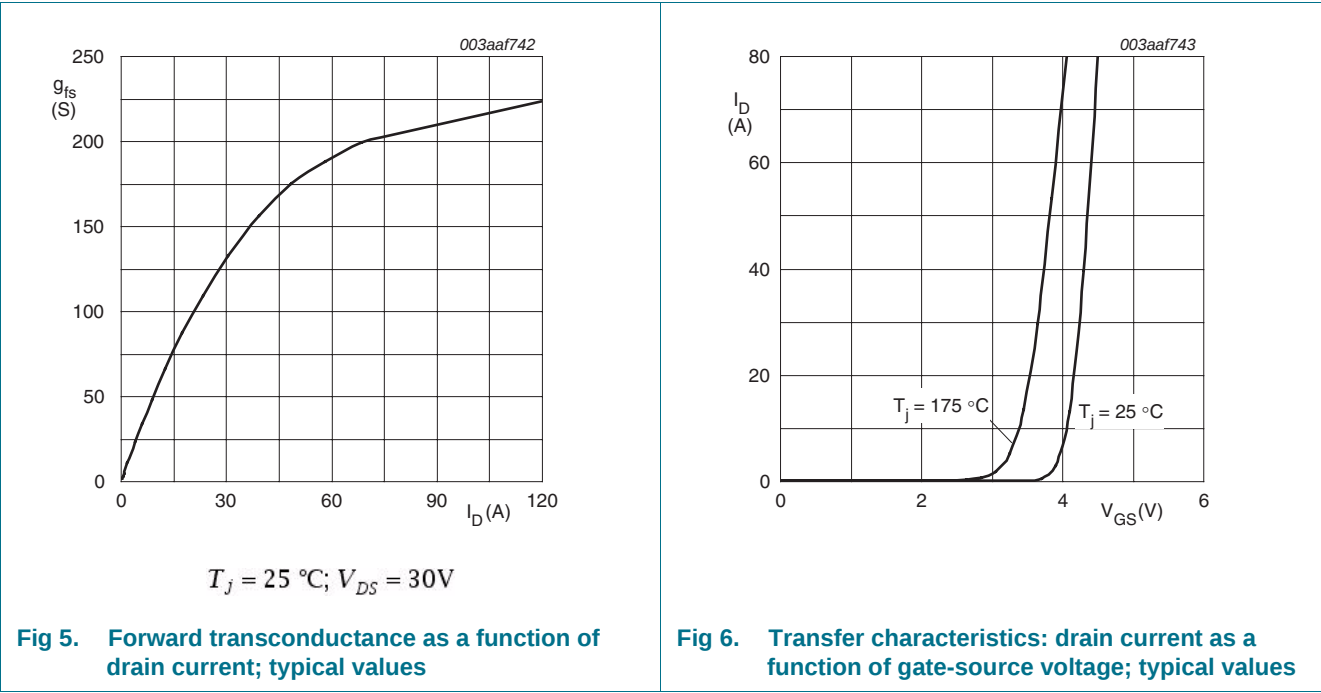
Table 6. Characteristics

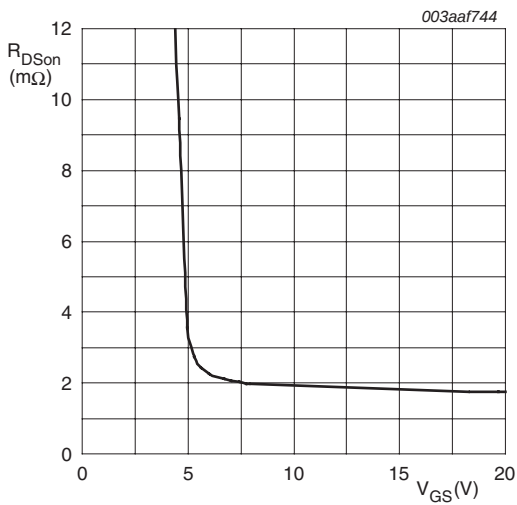
| Symbol                         | Parameter                         | Conditions                                                                                                                                   | Min              | Typ  | Max | Unit          |
|--------------------------------|-----------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|------------------|------|-----|---------------|
| <b>Static characteristics</b>  |                                   |                                                                                                                                              |                  |      |     |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage    | $I_D = 250\ \mu\text{A}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = -55\ ^\circ\text{C}$                                                              | 54               | -    | -   | V             |
|                                |                                   | $I_D = 250\ \mu\text{A}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                               | 60               | -    | -   | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage     | $I_D = 1\ \text{mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\ ^\circ\text{C}$ ; see <a href="#">Figure 10</a>                                       | -                | -    | 4.6 | V             |
|                                |                                   | $I_D = 1\ \text{mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175\ ^\circ\text{C}$ ; see <a href="#">Figure 10</a>                                       | 1                | -    | -   | V             |
|                                |                                   | $I_D = 1\ \text{mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\ ^\circ\text{C}$ ; see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>        | 2                | 3    | 4   | V             |
| $I_{DSS}$                      | drain leakage current             | $V_{DS} = 60\ \text{V}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                                | -                | 0.03 | 10  | $\mu\text{A}$ |
|                                |                                   | $V_{DS} = 60\ \text{V}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 175\ ^\circ\text{C}$                                                               | -                | -    | 500 | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current              | $V_{GS} = -20\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                               | -                | -    | 100 | nA            |
|                                |                                   | $V_{GS} = 20\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                                | -                | -    | 100 | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance  | $V_{GS} = 10\ \text{V}$ ; $I_D = 25\ \text{A}$ ; $T_j = 25\ ^\circ\text{C}$ ; see <a href="#">Figure 12</a>                                  | <sup>[1]</sup> - | 1.8  | 2.2 | mΩ            |
|                                |                                   | $V_{GS} = 10\ \text{V}$ ; $I_D = 25\ \text{A}$ ; $T_j = 175\ ^\circ\text{C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a> | -                | 4.3  | 5.1 | mΩ            |
|                                |                                   | $V_{GS} = 10\ \text{V}$ ; $I_D = 25\ \text{A}$ ; $T_j = 100\ ^\circ\text{C}$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a> | -                | 3    | 3.5 | mΩ            |
| $R_G$                          | gate resistance                   | $f = 1\ \text{MHz}$                                                                                                                          | -                | 0.9  | -   | Ω             |
| <b>Dynamic characteristics</b> |                                   |                                                                                                                                              |                  |      |     |               |
| $Q_{G(tot)}$                   | total gate charge                 | $I_D = 75\ \text{A}$ ; $V_{DS} = 30\ \text{V}$ ; $V_{GS} = 10\ \text{V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>     | -                | 137  | -   | nC            |
|                                |                                   | $I_D = 0\ \text{A}$ ; $V_{DS} = 0\ \text{V}$ ; $V_{GS} = 10\ \text{V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>       | -                | 129  | -   | nC            |
| $Q_{GS}$                       | gate-source charge                | $I_D = 75\ \text{A}$ ; $V_{DS} = 30\ \text{V}$ ; $V_{GS} = 10\ \text{V}$                                                                     | -                | 48   | -   | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge  | $I_D = 75\ \text{A}$ ; $V_{DS} = 30\ \text{V}$ ; $V_{GS} = 10\ \text{V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>     | -                | 29   | -   | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge |                                                                                                                                              | -                | 19   | -   | nC            |
| $Q_{GD}$                       | gate-drain charge                 |                                                                                                                                              | -                | 32   | -   | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage       | $V_{DS} = 30\ \text{V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>                                                      | -                | 5.7  | -   | V             |
| $C_{iss}$                      | input capacitance                 | $V_{DS} = 30\ \text{V}$ ; $V_{GS} = 0\ \text{V}$ ; $f = 1\ \text{MHz}$ ; $T_j = 25\ ^\circ\text{C}$ ; see <a href="#">Figure 16</a>          | -                | 9997 | -   | pF            |
| $C_{oss}$                      | output capacitance                |                                                                                                                                              | -                | 1210 | -   | pF            |
| $C_{rss}$                      | reverse transfer capacitance      |                                                                                                                                              | -                | 594  | -   | pF            |
| $t_{d(on)}$                    | turn-on delay time                | $V_{DS} = 30\ \text{V}$ ; $R_L = 0.4\ \Omega$ ; $V_{GS} = 10\ \text{V}$ ; $R_{G(ext)} = 4.7\ \Omega$ ; $I_D = 75\ \text{A}$                  | -                | 42   | -   | ns            |
| $t_r$                          | rise time                         |                                                                                                                                              | -                | 56   | -   | ns            |
| $t_{d(off)}$                   | turn-off delay time               |                                                                                                                                              | -                | 115  | -   | ns            |
| $t_f$                          | fall time                         |                                                                                                                                              | -                | 49   | -   | ns            |

Table 6. Characteristics ...continued

| Symbol             | Parameter             | Conditions                                                                                                   | Min | Typ | Max | Unit |
|--------------------|-----------------------|--------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| Source-drain diode |                       |                                                                                                              |     |     |     |      |
| $V_{SD}$           | source-drain voltage  | $I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>           | -   | 0.8 | 1.2 | V    |
| $t_{rr}$           | reverse recovery time | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$ | -   | 57  | -   | ns   |
| $Q_r$              | recovered charge      | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$ | -   | 80  | -   | nC   |

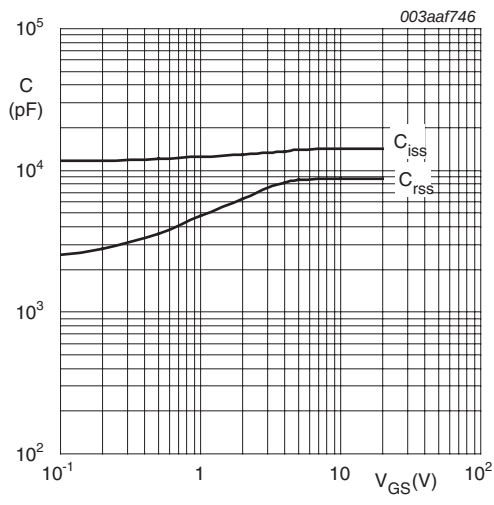
[1] Measured 3 mm from package.





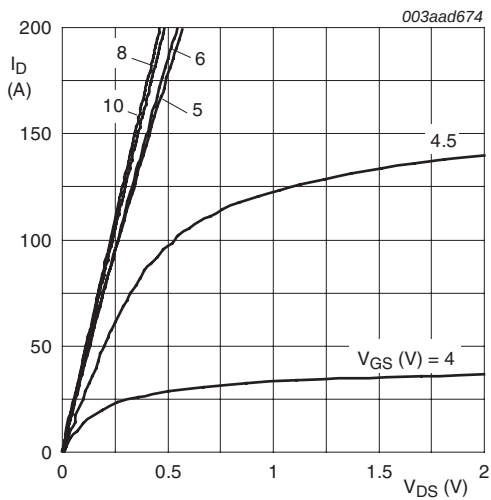
$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



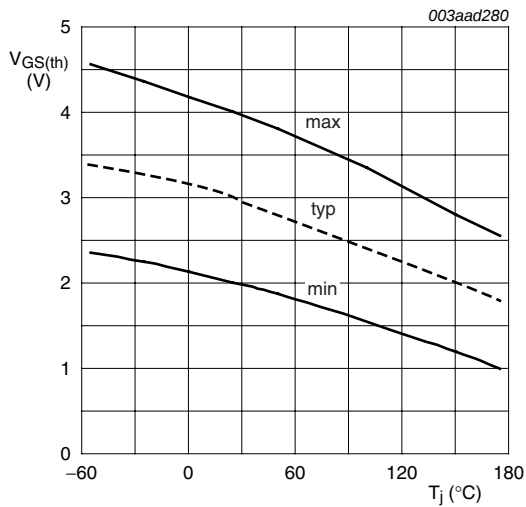
$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values



$T_j = 25\text{ }^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

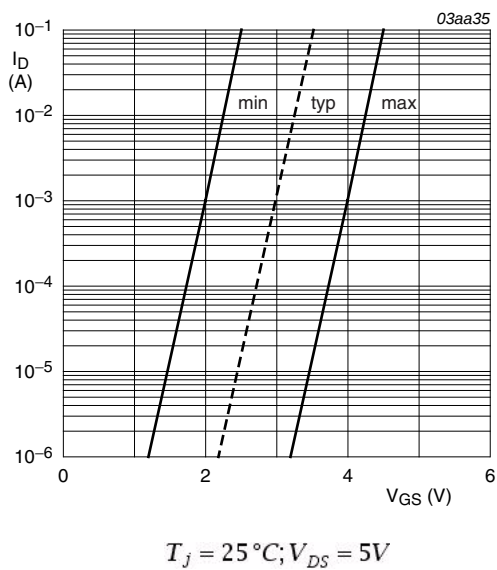


Fig 11. Sub-threshold drain current as a function of gate-source voltage

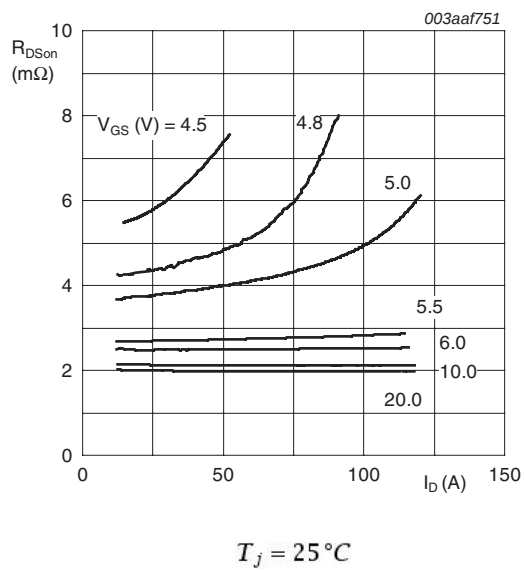


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

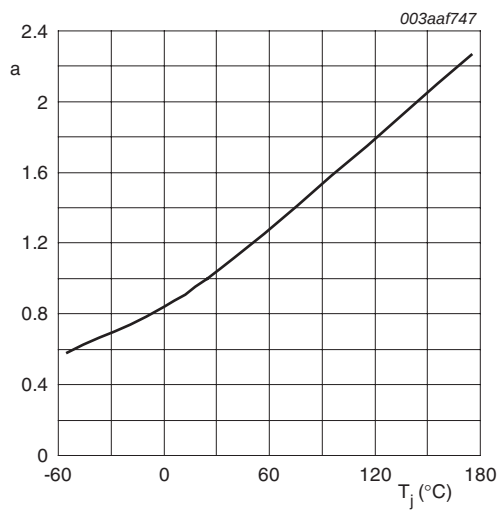


Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

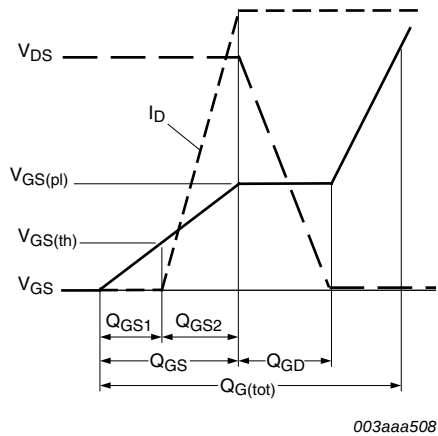
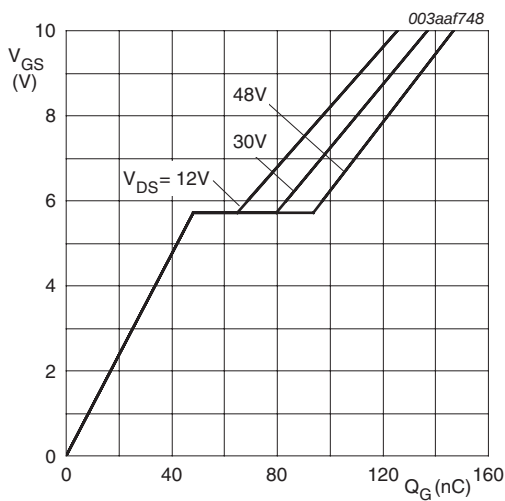
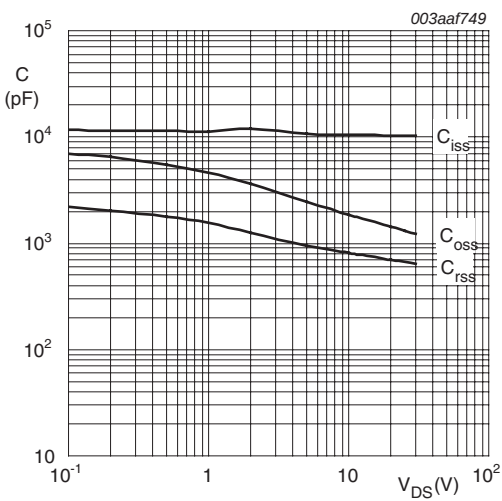


Fig 14. Gate charge waveform definitions



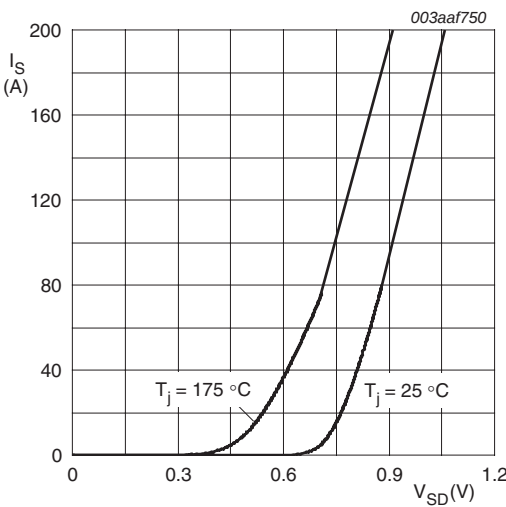
$T_J = 25\text{ }^{\circ}\text{C}; I_D = 75\text{ A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

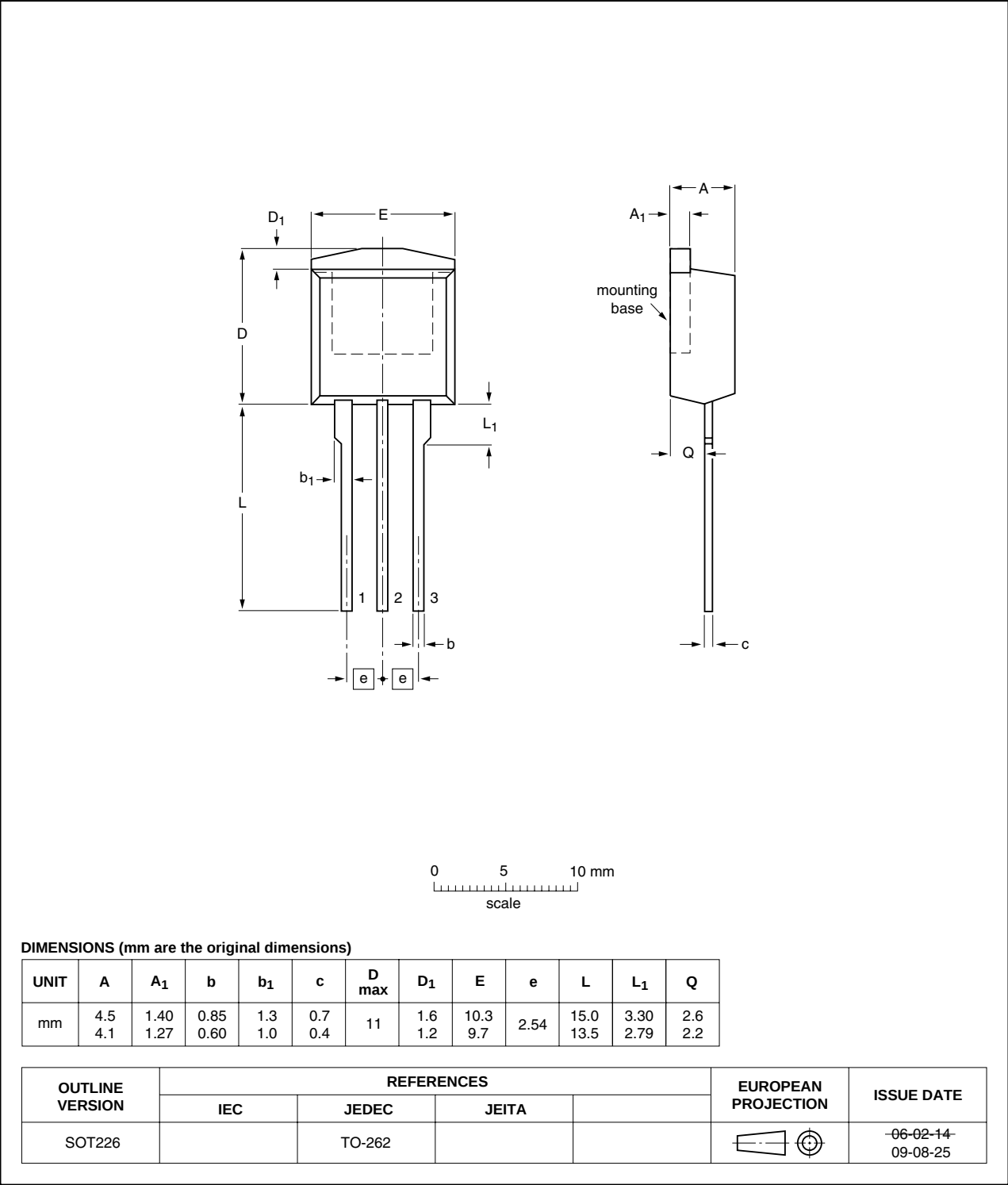


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

| Document ID      | Release date                                                                                                                  | Data sheet status    | Change notice | Supersedes       |
|------------------|-------------------------------------------------------------------------------------------------------------------------------|----------------------|---------------|------------------|
| PSMN2R0-60ES v.2 | 20110419                                                                                                                      | Product data sheet   | -             | PSMN2R0-60ES v.1 |
| Modifications:   | <ul style="list-style-type: none"><li>Status changed from objective to product.</li><li>Various changes to content.</li></ul> |                      |               |                  |
| PSMN2R0-60ES v.1 | 20110117                                                                                                                      | Objective data sheet | -             | -                |

## 9. Legal information

### 9.1 Data sheet status

| Document status <sup>[1] [2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|------------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet       | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet     | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet         | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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## 10. Contact information

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For sales office addresses, please send an email to: [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)

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